



#12 / 135
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R. Stiles

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No. 040373/0300

Applicant: Toshiyuki HIROTA et al.

Title: SEMICONDUCTOR DEVICE WITH HIGH- AND LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE

Serial No.: 09/741,195

Filed: December 21, 2000

Examiner: Vu, Quang D.

Art Unit: 2811

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INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §1.56 and 37 CFR §1.97

Commissioner for Patents
Washington, D.C. 20231

Sir:

Submitted herewith on Form PTO-SB/08 is a listing of documents known to Applicants in order to comply with Applicants' duty of disclosure pursuant to 37 CFR 1.56. A copy of each listed document is being submitted to comply with the provisions of 37 CFR 1.97 and 1.98.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is

determined to be a prima facie prior art reference against the claims of the present application.

TIMING OF THE DISCLOSURE

The instant Information Disclosure Statement is being filed before the mailing date of the final action under 37 C.F.R. §1.113. Accordingly, pursuant to 37 C.F.R. §1.97(c), a certification or fee is required. Applicant is providing a certification below in lieu of the fee.

CERTIFICATION

The undersigned hereby certifies in accordance with 37 C.F.R. §1.97(e)(1) that items of information A3 and A4 listed on the PTO/SB/08 form included with this Information Disclosure Statement were first cited in a communication from a foreign patent office in a counterpart foreign application not more than three (3) months prior to the filing of this Statement. Items of information A1 and A2 listed on the attached PTO/SB/08 form are U.S. patents that are counterparts to item of information A3.

RELEVANCE OF EACH DOCUMENT

A translation of a portion of a Korean Office Action that issued August 28, 2002 with respect to a counterpart Korean patent application is provided below.

"Grounds

The present invention is related to a method of manufacturing semiconductor device characterized in that the semiconductor device comprised with memory cell regions and logic circuits has nitride films and insulating films. However, Japanese Patent Publication No. 05-160362 (June 25, 1993) which concerns a method of manufacturing stacked DRAM formed from a memory cell art and a peripheral circuit part has a constitution comprising steps of forming silicon nitride film over the memory cell part and the peripheral circuit part; removing the insulating film and the silicon nitride film on the memory cell part

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after an insulating film is formed on the silicon nitride film; and etching the insulating film by using the nitride film remaining at the peripheral circuit part. Japanese Patent Publication No. 11-87653 (March 30, 1999) is related to a semiconductor device including a first region having a high pattern density, and a second region having a low pattern density characterized in that the second laminated insulating film and the fourth laminated insulating film are formed of nitride. According, the present invention is deemed to be easily invented by a person skilled in the pertinent art.

Attachments

Attached 1: Japanese Patent Publication No. 11-87653
(March 30, 1999)

Attached 2: Japanese Patent Publication No. 05-160362
(June 25, 1993)"

Applicant's statements regarding the Korean Office Action are based on a partial translation that Applicant's representative obtained. These statements should in no way be considered as an agreement by Applicant with, or an admission of, what is asserted in the Korean Office Action.

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Applicant respectfully requests that the listed documents be considered by the Examiner and formally be made of record in the present application and that an initialed copy of Form PTO SB/08 be returned in accordance with MPEP §609.

Respectfully submitted,

October 9, 2002
Date

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Should additional fees be necessary in connection with the filing of this paper, or if a petition for extension of time is required for timely acceptance of same, the Commissioner is hereby authorized to charge Deposit Account No. 19-0741 for any such fees; and applicant(s) hereby petition for any needed extension of time.